

# MC74LVX14

## Hex Schmitt Inverter

### With 5 V-Tolerant Inputs

The MC74LVX14 is an advanced high speed CMOS Schmitt inverter. The inputs tolerate voltages up to 7 V, allowing the interface of 5 V systems to 3 V systems.

The MC74LVX14 is pin and functionally compatible to the MC74LVX04, but the inputs have hysteresis and, with its Schmitt trigger function, can be used as a line receiver which will receive slow input signals.

#### Features

- High Speed:  $t_{PD} = 6.8 \text{ ns}$  (Typ) at  $V_{CC} = 3.3 \text{ V}$
- Low Power Dissipation:  $I_{CC} = 2 \mu\text{A}$  (Max) at  $T_A = 25^\circ\text{C}$
- Powerdown Protection Provided on Inputs
- Balanced Propagation Delays
- Low Noise:  $V_{OLP} = 0.5 \text{ V}$  (Max)
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- ESD Performance: Human Body Model > 2000 V;  
Machine Model > 200 V
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

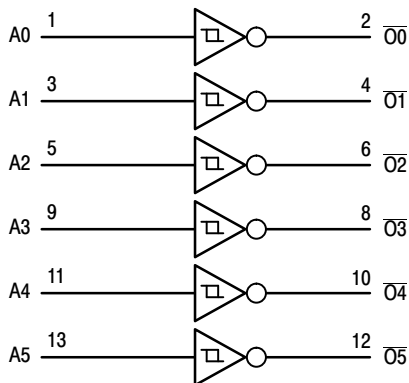


Figure 1. Logic Diagram

#### PIN NAMES

Pins	Function
$A_n$ $O_n$	Data Inputs Data Outputs

#### FUNCTION TABLE

$A_n$	$O_n$
L	H
H	L



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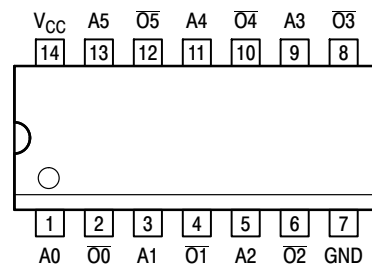


SOIC-14 NB  
D SUFFIX  
CASE 751A



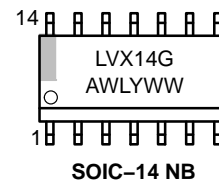
TSSOP-14  
DT SUFFIX  
CASE 948G

#### PIN ASSIGNMENT

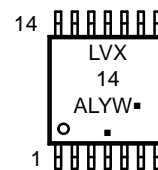


14-Lead (Top View)

#### MARKING DIAGRAMS



SOIC-14 NB



TSSOP-14

LVX14 = Specific Device Code  
A = Assembly Location  
WL, L = Wafer Lot  
Y = Year  
WW, W = Work Week  
G or ■ = Pb-Free Package

(Note: Microdot may be in either location)

#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.

# MC74LVX14

## MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
$V_{CC}$	DC Supply Voltage	-0.5 to +7.0	V
$V_{in}$	DC Input Voltage	-0.5 to +7.0	V
$V_{out}$	DC Output Voltage	-0.5 to $V_{CC} + 0.5$	V
$I_{IK}$	Input Diode Current	-20	mA
$I_{OK}$	Output Diode Current	$\pm 20$	mA
$I_{out}$	DC Output Current, per Pin	$\pm 25$	mA
$I_{CC}$	DC Supply Current, $V_{CC}$ and GND Pins	$\pm 50$	mA
$P_D$	Power Dissipation	180	mW
$T_{stg}$	Storage Temperature	-65 to +150	$^{\circ}C$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

## RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
$V_{CC}$	DC Supply Voltage	2.0	3.6	V
$V_{in}$	DC Input Voltage	0	5.5	V
$V_{out}$	DC Output Voltage	0	$V_{CC}$	V
$T_A$	Operating Temperature, All Package Types	-40	+85	$^{\circ}C$

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

## DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Conditions	$V_{CC}$ V	$T_A = 25^{\circ}C$			$T_A = -40$ to $85^{\circ}C$		Unit
				Min	Typ	Max	Min	Max	
$V_{T+}$	Positive Threshold Voltage (Figure 4)		3.0			2.20		2.20	V
$V_{T-}$	Negative Threshold Voltage (Figure 4)		3.0	0.90			0.90		V
$V_H$	Hysteresis Voltage (Figure 4)		3.0	0.30		1.20	0.30	1.20	V
$V_{OH}$	High-Level Output Voltage ( $V_{in} = V_{IH}$ or $V_{IL}$ )	$I_{OH} = -50 \mu A$	2.0	1.9	2.0		1.9		V
		$I_{OH} = -50 \mu A$	3.0	2.9	3.0		2.9		
		$I_{OH} = -4 mA$	3.0	2.58			2.48		
$V_{OL}$	Low-Level Output Voltage ( $V_{in} = V_{IH}$ or $V_{IL}$ )	$I_{OL} = 50 \mu A$	2.0		0.0	0.1		0.1	V
		$I_{OL} = 50 \mu A$	3.0		0.0	0.1		0.1	
		$I_{OL} = 4 mA$	3.0			0.36		0.44	
$I_{in}$	Input Leakage Current	$V_{in} = 5.5 V$ or GND	3.6			$\pm 0.1$		$\pm 1.0$	$\mu A$
$I_{CC}$	Quiescent Supply Current	$V_{in} = V_{CC}$ or GND	3.6			2.0		20.0	$\mu A$

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

## AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0 ns$ )

Symbol	Parameter	Test Conditions	$T_A = 25^{\circ}C$			$T_A = -40$ to $85^{\circ}C$		Unit
			Min	Typ	Max	Min	Max	
$t_{PLH}$ , $t_{PHL}$	Propagation Delay, Input-to-Output	$V_{CC} = 2.7 V$ $C_L = 15 pF$ $C_L = 50 pF$		8.7 11.2	16.3 19.8	1.0 1.0	19.5 23.0	ns
		$V_{CC} = 3.3 \pm 0.3 V$ $C_L = 15 pF$ $C_L = 50 pF$		6.8 9.3	10.6 14.1	1.0 1.0	12.5 16.0	
$t_{OSHL}$ $t_{OSLH}$	Output-to-Output Skew (Note 1)	$V_{CC} = 2.7 V$ $C_L = 50 pF$			1.5		1.5	ns
		$V_{CC} = 3.3 \pm 0.3 V$ $C_L = 50 pF$			1.5		1.5	

1. Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device. The specification applies to any outputs switching in the same direction, either HIGH-to-LOW ( $t_{OSHL}$ ) or LOW-to-HIGH ( $t_{OSLH}$ ); parameter guaranteed by design.

# MC74LVX14

## CAPACITIVE CHARACTERISTICS

Symbol	Parameter	T <sub>A</sub> = 25°C			T <sub>A</sub> = -40 to 85°C		Unit
		Min	Typ	Max	Min	Max	
C <sub>in</sub>	Input Capacitance		4	10		10	pF
C <sub>PD</sub>	Power Dissipation Capacitance (Note 2)		21				pF

2. C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation:  $I_{CC(OPR)} = C_{PD} \cdot V_{CC} \cdot f_{in} + I_{CC}/6$  (per buffer). C<sub>PD</sub> is used to determine the no-load dynamic power consumption;  $P_D = C_{PD} \cdot V_{CC}^2 \cdot f_{in} + I_{CC} \cdot V_{CC}$ .

## NOISE CHARACTERISTICS (Input t<sub>r</sub> = t<sub>f</sub> = 3.0 ns, C<sub>L</sub> = 50 pF, V<sub>CC</sub> = 3.3 V, Measured in SOIC Package)

Symbol	Characteristic	T <sub>A</sub> = 25°C		Unit
		Typ	Max	
V <sub>OLP</sub>	Quiet Output Maximum Dynamic V <sub>OL</sub>	0.3	0.5	V
V <sub>OLV</sub>	Quiet Output Minimum Dynamic V <sub>OL</sub>	-0.3	-0.5	V
V <sub>IHD</sub>	Minimum High Level Dynamic Input Voltage		2.0	V
V <sub>ILD</sub>	Maximum Low Level Dynamic Input Voltage		0.9	V

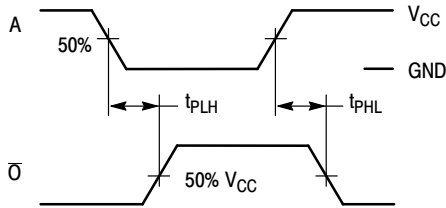
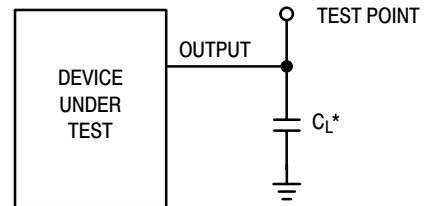


Figure 2. Switching Waveforms



\*Includes all probe and jig capacitance

Figure 3. Test Circuit

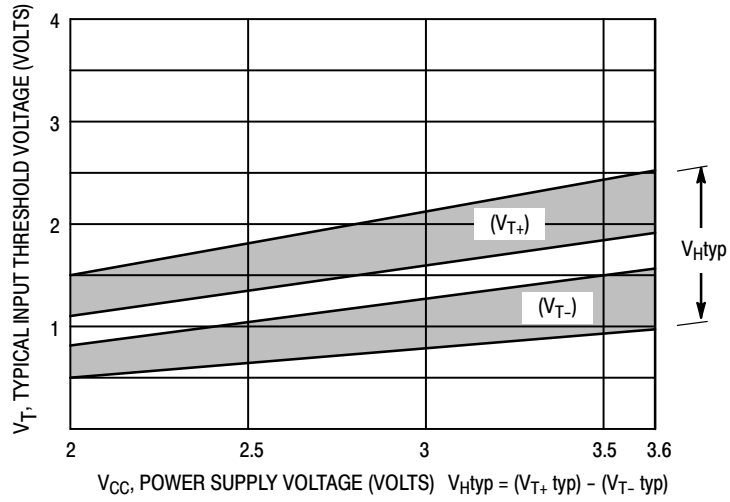
## ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
MC74LVX14DR2G	SOIC-14 NB (Pb-Free)	2500 Tape & Reel
MC74LVX14DTR2G	TSSOP-14 (Pb-Free)	2500 Tape & Reel
NLV74LVX14DTR2G*	TSSOP-14 (Pb-Free)	2500 Tape & Reel

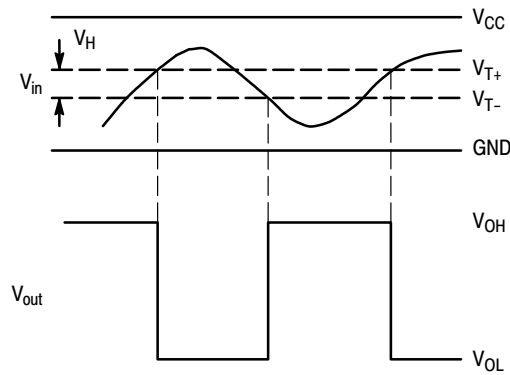
<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

\*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

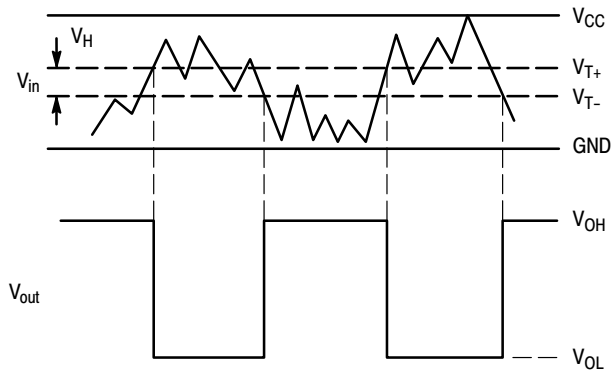
# MC74LVX14



**Figure 4. Typical Input Threshold,  $V_{T+}$ ,  $V_{T-}$  versus Power Supply Voltage**



(a) A Schmitt-Trigger Squares Up Inputs With Slow Rise and Fall Times



(b) A Schmitt-Trigger Offers Maximum Noise Immunity

**Figure 5. Typical Schmitt-Trigger Applications**

# MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



SCALE 1:1

SOIC-14 NB  
CASE 751A-03  
ISSUE L

DATE 03 FEB 2016



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF AT MAXIMUM MATERIAL CONDITION.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSIONS.
5. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	1.35	1.75	0.054	0.068
A1	0.10	0.25	0.004	0.010
A3	0.19	0.25	0.008	0.010
b	0.35	0.49	0.014	0.019
D	8.55	8.75	0.337	0.344
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.019
L	0.40	1.25	0.016	0.049
M	0°	7°	0°	7°

SOLDERING FOOTPRINT\*



DIMENSIONS: MILLIMETERS

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM\*



- XXXXXX = Specific Device Code
- A = Assembly Location
- WL = Wafer Lot
- Y = Year
- WW = Work Week
- G = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

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**SOIC-14**  
**CASE 751A-03**  
**ISSUE L**

DATE 03 FEB 2016

STYLE 1:  
 PIN 1. COMMON CATHODE  
 2. ANODE/CATHODE  
 3. ANODE/CATHODE  
 4. NO CONNECTION  
 5. ANODE/CATHODE  
 6. NO CONNECTION  
 7. ANODE/CATHODE  
 8. ANODE/CATHODE  
 9. ANODE/CATHODE  
 10. NO CONNECTION  
 11. ANODE/CATHODE  
 12. ANODE/CATHODE  
 13. NO CONNECTION  
 14. COMMON ANODE

STYLE 2:  
 CANCELLED

STYLE 3:  
 PIN 1. NO CONNECTION  
 2. ANODE  
 3. ANODE  
 4. NO CONNECTION  
 5. ANODE  
 6. NO CONNECTION  
 7. ANODE  
 8. ANODE  
 9. ANODE  
 10. NO CONNECTION  
 11. ANODE  
 12. ANODE  
 13. NO CONNECTION  
 14. COMMON CATHODE

STYLE 4:  
 PIN 1. NO CONNECTION  
 2. CATHODE  
 3. CATHODE  
 4. NO CONNECTION  
 5. CATHODE  
 6. NO CONNECTION  
 7. CATHODE  
 8. CATHODE  
 9. CATHODE  
 10. NO CONNECTION  
 11. CATHODE  
 12. CATHODE  
 13. NO CONNECTION  
 14. COMMON ANODE

STYLE 5:  
 PIN 1. COMMON CATHODE  
 2. ANODE/CATHODE  
 3. ANODE/CATHODE  
 4. ANODE/CATHODE  
 5. ANODE/CATHODE  
 6. NO CONNECTION  
 7. COMMON ANODE  
 8. COMMON CATHODE  
 9. ANODE/CATHODE  
 10. ANODE/CATHODE  
 11. ANODE/CATHODE  
 12. ANODE/CATHODE  
 13. NO CONNECTION  
 14. COMMON ANODE

STYLE 6:  
 PIN 1. CATHODE  
 2. CATHODE  
 3. CATHODE  
 4. CATHODE  
 5. CATHODE  
 6. CATHODE  
 7. CATHODE  
 8. ANODE  
 9. ANODE  
 10. ANODE  
 11. ANODE  
 12. ANODE  
 13. ANODE  
 14. ANODE

STYLE 7:  
 PIN 1. ANODE/CATHODE  
 2. COMMON ANODE  
 3. COMMON CATHODE  
 4. ANODE/CATHODE  
 5. ANODE/CATHODE  
 6. ANODE/CATHODE  
 7. ANODE/CATHODE  
 8. ANODE/CATHODE  
 9. ANODE/CATHODE  
 10. ANODE/CATHODE  
 11. COMMON CATHODE  
 12. COMMON ANODE  
 13. ANODE/CATHODE  
 14. ANODE/CATHODE

STYLE 8:  
 PIN 1. COMMON CATHODE  
 2. ANODE/CATHODE  
 3. ANODE/CATHODE  
 4. NO CONNECTION  
 5. ANODE/CATHODE  
 6. ANODE/CATHODE  
 7. COMMON ANODE  
 8. COMMON ANODE  
 9. ANODE/CATHODE  
 10. ANODE/CATHODE  
 11. NO CONNECTION  
 12. ANODE/CATHODE  
 13. ANODE/CATHODE  
 14. COMMON CATHODE

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# MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



**TSSOP-14 WB**  
CASE 948G  
ISSUE C

DATE 17 FEB 2016

SCALE 2:1



**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.90	5.10	0.193	0.200
B	4.30	4.50	0.169	0.177
C	---	1.20	---	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8°

**GENERIC MARKING DIAGRAM\***



- A = Assembly Location
- L = Wafer Lot
- Y = Year
- W = Work Week
- = Pb-Free Package

(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



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